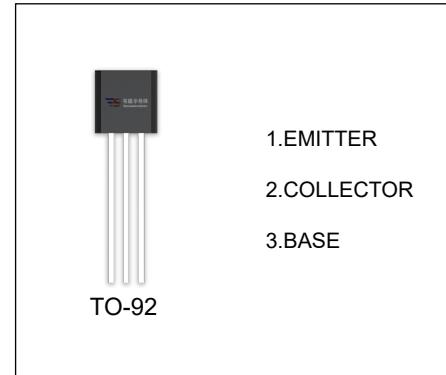


KSC815 TRANSISTOR (NPN)

FEATURES

- Low Collector Current
- Complement To KSA539
- Low Frequency Amplifier & High Frequency Oscillator



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
KSC815	TO-92	Bulk	1000pcs/Bag
KSC815-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_c	Collector Current	0.2	A
P_c	Collector Power Dissipation	400	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	312	°C/W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

T_a=25 °C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 0.1mA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.01mA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =45V, I _E =0			0.1	µA
Emitter cut-off current	I _{EBO}	V _{EB} =3V, I _C =0			0.1	µA
DC current gain	h _{FE}	V _{CE} =1V, I _C =50mA	40		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =150mA, I _B =15mA			0.4	V
Base-emitter saturation voltage	V _{BE (sat)}	I _C =150mA, I _B =15mA			1.1	V
Base-emitter voltage	V _{BE}	V _{CE} =10V, I _C =10mA	0.6		0.9	V
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		4		pF
Transition frequency	f _T	V _{CE} =10V, I _C = 10mA	100			MHz

CLASSIFICATION OF h_{FE}

RANK	R	O	Y	G
RANGE	40-80	70-140	120-240	200-400